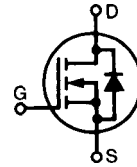


MegaMOS™FET

IXTH / IXTM 10N100
IXTH / IXTM 12N100

V_{DSS}	I_{D25}	$R_{DS(on)}$
1000 V	10 A	1.20 Ω
1000 V	12 A	1.05 Ω

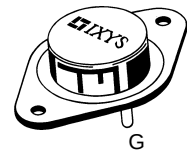
N-Channel Enhancement Mode



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	1000	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	1000	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	10N100: 10 12N100: 12	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	10N100: 40 12N100: 48	A
P_D	$T_C = 25^\circ\text{C}$	300	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		TO-204 = 18 g, TO-247 = 6 g	
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-247 AD (IXTH)

TO-204 AA (IXTM)



G = Gate,
S = Source,

D = Drain,
TAB = Drain

Features

- International standard packages
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Low package inductance (< 5 nH)
 - easy to drive and to protect
- Fast switching times

Applications

- Switch-mode and resonant-mode power supplies
- Motor controls
- Uninterruptible Power Supplies (UPS)
- DC choppers

Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

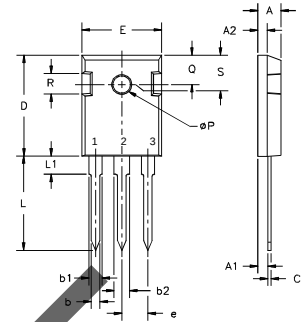
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 3\text{ mA}$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2		4.5 V
I_{GSS}	$V_{GS} = \pm 20\text{ V}_{DC}$, $V_{DS} = 0$			$\pm 100\text{ nA}$
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$ $V_{GS} = 0\text{ V}$			250 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $d \leq 2\%$			1.20 Ω 1.05 Ω

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test	6	12	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4000	pF
C_{oss}			310	pF
C_{rss}			70	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 2\ \Omega$, (External)		21	50 ns
t_r			33	50 ns
$t_{d(off)}$			62	100 ns
t_f			32	50 ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$		150	170 nC
Q_{gs}			30	45 nC
Q_{gd}			55	80 nC
R_{thJC}			0.25	0.42 K/W
R_{thCK}				K/W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$	10N100 12N100		10 A 12 A
I_{SM}	Repetitive; pulse width limited by T_{JM}	10N100 12N100		40 A 48 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		1000	ns

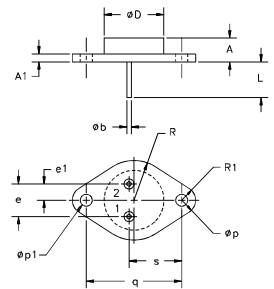
TO-247 AD (IXTH) Outline



Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-204AA (IXTM) Outline



Pins 1 - Gate 2 - Source
Case - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	6.4	11.4	.250	.450
A ₁		3.42		.135
Øb	.97	1.09	.038	.043
ØD		22.22		.875
e	10.67	11.17	.420	.440
e ₁	5.21	5.71	.205	.225
L	7.93		.312	
Øp	3.84	4.19	.151	.165
Øp ₁	3.84	4.19	.151	.165
q		30.15		1.187 BSC
R		13.33		.525
R ₁		4.77		.188
s	16.64	17.14	.655	.675

Fig. 1 Output Characteristics

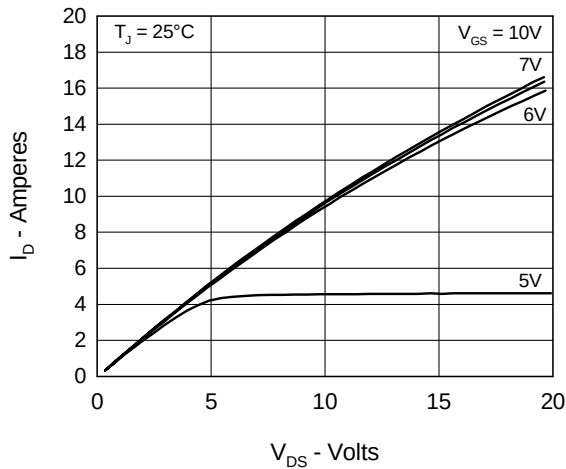


Fig. 2 Input Admittance

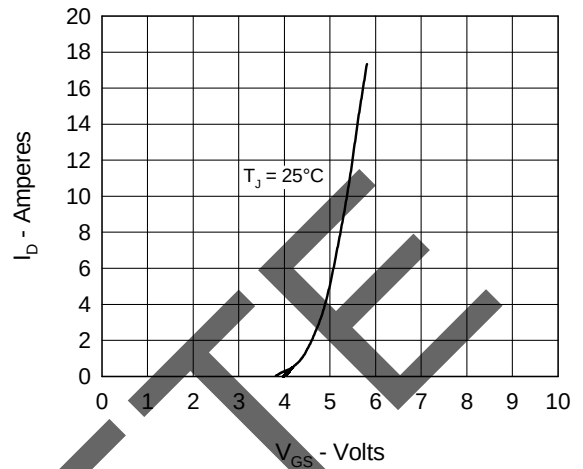


Fig. 3 $R_{DS(on)}$ vs. Drain Current

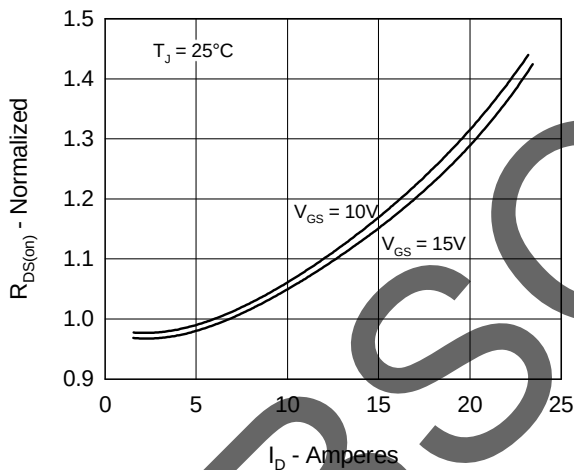


Fig. 4 Temperature Dependence of Drain to Source Resistance

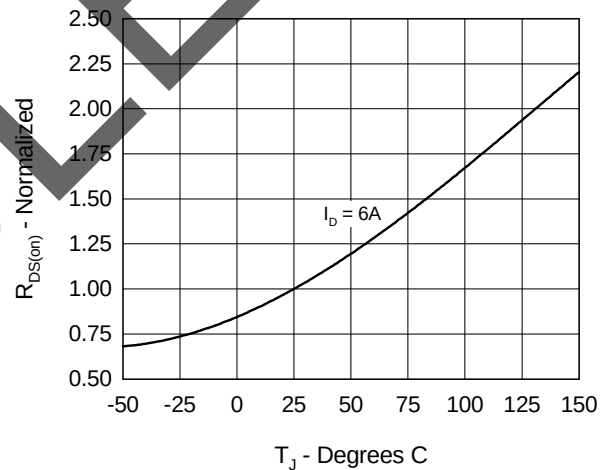


Fig. 5 Drain Current vs. Case Temperature

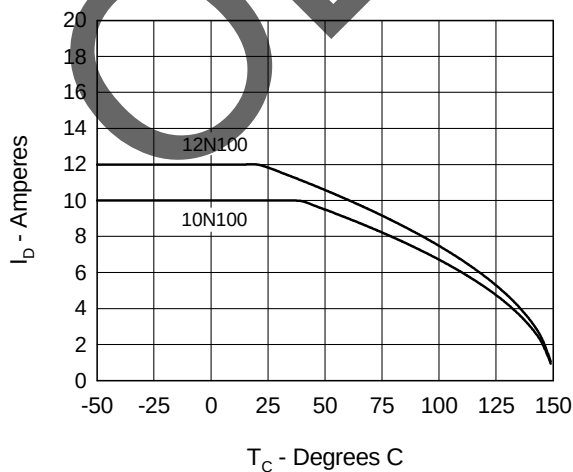


Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage

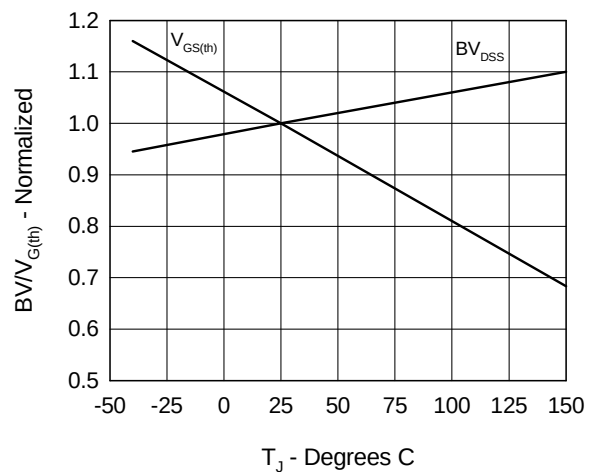


Fig.7 Gate Charge Characteristic Curve

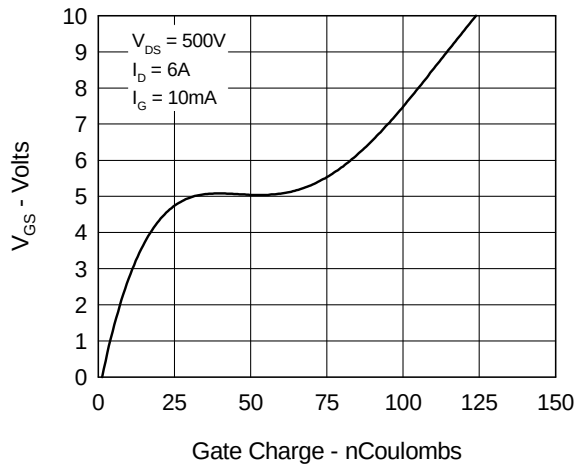


Fig.9 Capacitance Curves

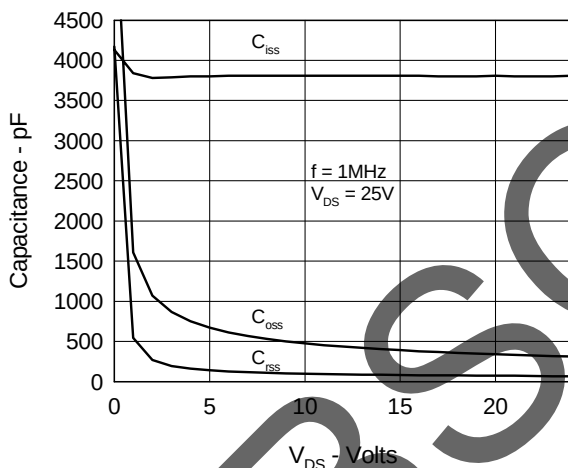


Fig.11 Transient Thermal Impedance

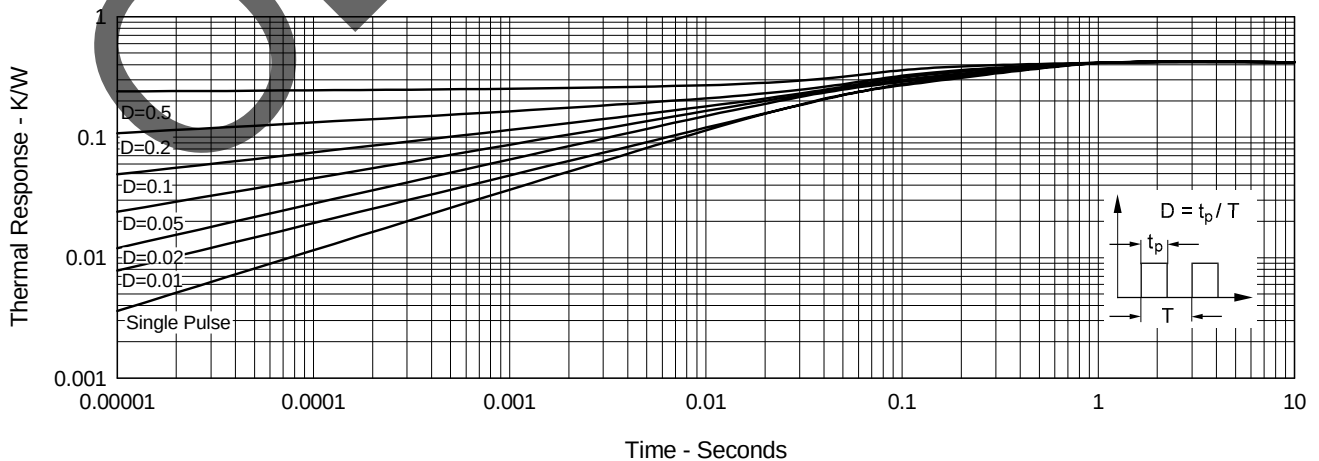


Fig.8 Forward Bias Safe Operating Area

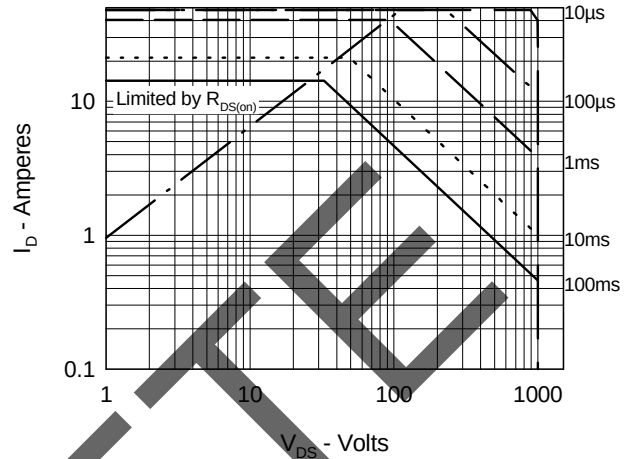


Fig.10 Source Current vs. Source to Drain Voltage

